# **Precision Micro-Power Shunt Voltage References**

### Description

LM4040 and LM4041 are precision two-terminal shunt mode voltage references offered in factory programmed reverse breakdown voltages of 1.225 V, 2.500 V, 3.000 V, 3.300 V, 4.096 V, and 5.000 V.

ON Semiconductor's Charge Programmable floating gate technology ensures precise voltage settings offering five grades of initial accuracy; from 0.1% to 2%.

LM4040 and LM4041 operate over a shunt current range of 60  $\mu$ A to 15 mA with low dynamic impedance, and 100 ppm/°C temperature coefficient ensuring stable reverse breakdown voltage accuracy over a wide range of operating conditions.

These shunt regulators do not require an external stabilizing capacitor but are stable with any capacitive load (up to  $1 \mu$ F).

Offered in space saving SOT-23 and SC-70 packages LM4040 and LM4041 are specified for operation over the full industrial temperature range of  $-40^{\circ}$ C to  $+85^{\circ}$ C.

### Features

- Reverse Breakdown Voltages:
  - ♦ 1.225 V
  - ◆ 2.500 V
    ◆ 3.000 V
- ◆ 4.096 V
  ◆ 5.000 V

♦ 3.300 V

◆ D: ±1.0%

◆ E: ±2.0%

- Accuracy Grades:
  - ♦ A: ±0.1%
  - ♦ B: ±0.2%
  - ♦ C: ±0.5%
- Operating Current: 60 µA to 15 mA
- Low Output Noise: 35 μV (10 Hz to 10 KHz)
- Small Package Size: SOT-23, SC-70
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **Typical Applications**

- Mobile Handheld Devices
- Industrial Process Control
- Instrumentation
- Laptop and Desktop PCs
- Automotive
- Energy Management



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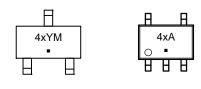
SOT-23 3 Lead TB SUFFIX CASE 527AG

A Y

M

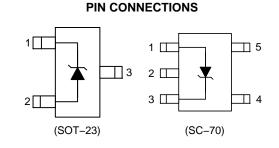
SC-70 5 Lead SD SUFFIX CASE 419AC

### MARKING DIAGRAMS



4x = Specific Device Code

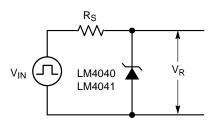
- (4L = LM4040, 4M = LM4041) = Assembly Location Code
- = Production Year
- = Production Month
- = Pb-Free Package
- = FD-Flee Fackage



### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

Semiconductor Components Industries, LLC, 2015 January, 2015 – Rev. 5



### Figure 1. Test Circuit

#### **Table 1. PIN DESCRIPTIONS**

Pin			
SOT-23	SC-70	Name	Function
1	3	V+	Positive voltage
2	1	V–	Negative voltage
3	2	NC	This pin must be left floating or connected to V
	4	NIC	No Internal Connection. A voltage or signal applied to this pin will have no effect.
	5	NIC	

### Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Unit
Reverse Current	20	mA
Forward Current	10	mA
Junction Temperature	150	°C
Power Dissipation SOT-23-3	300	mW
Power Dissipation SC-70-5	240	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Table 3. RECOMMENDED OPERATING CONDITIONS**

Parameter	Rating	Unit
IREVERSE	0.06 – 15	mA
Ambient Temperature Range	-40 to +85	°C

#### Table 4. ESD SUSCEPTABILITY

Symbol	Parameter	Min	Units
ESD	Human Body Model	2000	V
	Machine Model	200	V

### Table 5. DC ELECTRICAL CHARACTERISTICS

(I\_R = 100  $\mu$ A, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

					Limits		
Symbol	Parameter	Test Conditions		Min	Тур	Max	Units
.225 V							
V <sub>R</sub>	Reverse Breakdown Voltage	T <sub>A</sub> = +25°C	LM4041A (0.1%)	1.2238	1.225	1.2262	V
			LM4041B (0.2%)	1.2226	1.225	1.2274	
			LM4041C (0.5%)	1.219	1.225	1.231	
			LM4041D (1.0%)	1.213	1.225	1.237	
			LM4041E (2.0%)	1.200	1.225	1.250	
V <sub>R</sub>	Reverse Breakdown Voltage	LM4041A			±1.2	±9.2	mV
	Tolerance	LM4041B			±2.4	±10.4	
		LM4041C			±6	±14	
		LM4041D			±12	±24	
		LM4041E			±25	±36	
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ
$\Delta V_R / \Delta T$ Reverse Breakdown Voltage		I <sub>R</sub> = 10 mA			±20		ppm/°C
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4041A, B, C		±15	±100	
			LM4041D, E		±15	±150	
		I <sub>R</sub> = 100 μA	•		±15		
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_{MIN}} \leq I_{R} \leq$	LM4041A, B, C		0.7	2.0	mV
	Change with Operating Current	1 mA	LM4041D, E		0.7	2.5	
		1 mA ≤ I <sub>R</sub> ≤	LM4041A, B, C		2.5	8	
		15 mA	LM4041D, E		2.5	10	
Z <sub>R</sub>	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4041A, B		0.5	1.5	Ω
		f = 120 Hz, $I_{AC} = 0.1 I_{R}$	LM4041C		0.5	1.5	
			LM4041D, E		0.5	2.0	
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	) Hz ≤ f ≤ 10 KHz	l	200		μV <sub>RMS</sub>
$\Delta V_{R}$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	+125°C		0.08		%

V <sub>R</sub>	Reverse Breakdown Voltage	$T_A = +25^{\circ}C$	LM4040A (0.1%)	2.498	2.500	2.502	V
			LM4040B (0.2%)	2.496	2.500	2.504	
			LM4040C (0.5%)	2.490	2.500	2.510	
			LM4040D (1.0%)	2.475	2.500	2.525	
			LM4040E (2.0%)	2.450	2.500	2.550	
V <sub>R</sub>	Reverse Breakdown Voltage Tolerance	LM4040A			±2	±19	mV
	Tolerance	LM4040B			±4	±21	
		LM4040C			±10	±29	
		LM4040D			±25	±49	
		LM4040E			±50	±74	

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

### Table 5. DC ELECTRICAL CHARACTERISTICS

(I<sub>R</sub> = 100  $\mu$ A, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

					Limits			
Symbol	Parameter	Test (	Conditions	Min	Тур	Max	Units	
2.500 V		•						
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ	
$\Delta V_{R} / \Delta T$	Reverse Breakdown Voltage	I <sub>R</sub> = 10 mA			±20		ppm/°C	
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4040A, B, C		±15	±100	1	
			LM4040D, E		±15	±150	1	
		I <sub>R</sub> = 100 μA			±15		1	
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_MIN} \le I_R \le$	LM4040A, B, C		0.3	1.0	mV	
	Change with Operating Current	1 mA	LM4040D, E		0.3	1.2	1	
		$1 \text{ mA} \leq I_R \leq$	LM4040A, B, C		2.5	8	1	
		15 mA	LM4040D, E		2.5	10	1	
Z <sub>R</sub>	Reverse Dynamic Impedance	I <sub>R</sub> = 1 mA,	LM4040A, B		0.3	0.8	Ω	
		f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	LM4040C		0.3	0.9	1	
			LM4040D, E		0.3	1.1	1	
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	) Hz ≤ f ≤ 10 KHz		350		μV <sub>RMS</sub>	
$\Delta V_{R}$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm	
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	+125°C		0.08		%	
3.000 V								
V <sub>R</sub>	Reverse Breakdown Voltage	$T_A = +25^{\circ}C$	LM4040A (0.1%)	2.997	3.000	3.003	V	
			LM4040B (0.2%)	2.994	3.000	3.006	1	
			LM4040C (0.5%)	2.985	3.000	3.015	1	
			LM4040D (1.0%)	2.970	3.000	3.030		
			LM4040E (2.0%)	2.940	3.000	3.060		
V <sub>R</sub>	Reverse Breakdown Voltage	LM4040A	1		±3	±22	mV	
	Tolerance	LM4040B			±6	±26	1	
		LM4040C			±15	±34	1	
		LM4040D			±30	±59	1	
		LM4040E			±60	±89	1	
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ	
$\Delta V_{R} / \Delta T$	Reverse Breakdown Voltage	I <sub>R</sub> = 10 mA			±20		ppm/°C	
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4040A, B, C		±15	±100	1	
			LM4040D, E		±15	±150	1	
		I <sub>R</sub> = 100 uA	1		±15		1	
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_{MIN}} \le I_{R} \le$	LM4040A, B, C		0.4	1.1	mV	
	Change with Operating Current	1 mA	LM4040D, E		0.4	1.3	1	
		$1mA \le I_R \le$	LM4040A, B, C		2.7	9	1	
		15 mA	LM4040D, E		2.7	11	-	

 Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature –40°C and the 25°C measurement after cycling to temperature +125°C.

Table 5. DC ELECTRICAL CHARACTERISTICS $(I_R = 100 \ \mu A, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted. Typical values are at } T_A = +25^{\circ}C.)$ 

					Limits		
Symbol	Parameter	Test C	Conditions	Min	Тур	Max	Units
3.000 V		-					
Z <sub>R</sub>	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.4	0.9	Ω
		f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	LM4040C		0.4	0.9	1
			LM4040D, E		0.4	1.2	
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	$Hz \le f \le 10 \text{ KHz}$		350		μV <sub>RMS</sub>
$\Delta V_{R}$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	+125°C		0.08		%
.300 V							
V <sub>R</sub>	Reverse Breakdown Voltage	T <sub>A</sub> = +25°C	LM4040A (0.1%)	3.297	3.300	3.303	V
			LM4040B (0.2%)	3.294	3.300	3.306	1
V <sub>R</sub>	Reverse Breakdown Voltage	T <sub>A</sub> = +25°C	LM4040C (0.5%)	3.285	3.300	3.315	V
			LM4040D (1.0%)	3.270	3.300	3.330	
V <sub>R</sub>	Reverse Breakdown Voltage	LM4040A			±3	±22	mV
	Tolerance	LM4040B			±6	±26	1
		LM4040C			±15	±34	1
		LM4040D			±30	±59	-
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ
$\Delta V_{R} / \Delta T$	Reverse Breakdown Voltage	I <sub>R</sub> = 10 mA			±20		ppm/°C
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4040A, B, C		±15	±100	1
			LM4040D		±15	±150	-
		I <sub>R</sub> = 100 μA	•		±15		1
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_{MIN}} \leq I_{R} \leq$	LM4040A, B, C		0.3	1.0	mV
	Change with Operating Current	1 mA	LM4040D		0.3	1.2	1
		$1 \text{ mA} \leq I_R \leq$	LM4040A, B, C		2.5	8	1
		15 mA	LM4040D		2.5	10	1
Z <sub>R</sub>	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.3	0.8	Ω
		f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	LM4040C		0.3	0.9	1
			LM4040D		0.3	1.1	1
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	$Hz \le f \le 10 \text{ KHz}$		350		μV <sub>RMS</sub>
$\Delta V_R$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	±125°C		0.08		%

V <sub>R</sub>	Reverse Breakdown Voltage	$T_A = +25^{\circ}C$	LM4040A (0.1%)	4.092	4.096	4.100	V
			LM4040B (0.2%)	4.088	4.096	4.104	
			LM4040C (0.5%)	4.080	4.096	4.120	
			LM4040D (1.0%)	4.055	4.096	4.137	

Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

### Table 5. DC ELECTRICAL CHARACTERISTICS

(I<sub>R</sub> = 100  $\mu$ A, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

					Limits		
Symbol	Parameter	Test C	Conditions	Min	Тур	Max	Units
1.096 V							
V <sub>R</sub>	Reverse Breakdown Voltage	LM4040A			±4	±31	mV
	Tolerance	LM4040B			±8	±35	
		LM4040C			±20	±47	1
		LM4040D			±41	±80	1
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ
$\Delta V_R / \Delta T$	Reverse Breakdown Voltage	I <sub>R</sub> = 10 mA			±30		ppm/°0
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4040A, B, C		±20	±100	1
			LM4040D		±20	±150	
		I <sub>R</sub> = 100 μA			±15		
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R}MIN} \le I_R \le$	LM4040A, B, C		0.5	1.2	mV
	Change with Operating Current	1 mA	LM4040D		0.5	1.5	
		$1 \text{ mA} \leq I_R \leq$	LM4040A, B, C		3.0	10	1
		15 mA	LM4040D		3.0	13	1
Z <sub>R</sub>	Reverse Dynamic Impedance	$I_R = 1 \text{ mA},$	LM4040A, B		0.5	1.0	Ω
		f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	LM4040C		0.5	1.0	1
			LM4040D		0.5	1.3	1
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	$Hz \le f \le 10 \text{ KHz}$		800		μV <sub>RMS</sub>
$\Delta V_R$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	+125°C		0.08		%
5.000 V							

V <sub>R</sub>	Reverse Breakdown Voltage	$T_A = +25^{\circ}C$	LM4040A (0.1%)	4.995	5.000	5.005	V
			LM4040B (0.2%)	4.990	5.000	5.010	
			LM4040C (0.5%)	4.975	5.000	5.025	
			LM4040D (1.0%)	4.950	5.000	5.050	
V <sub>R</sub>	V <sub>R</sub> Reverse Breakdown Voltage Tolerance				±5	±38	mV
	Tolerance	LM4040B	LM4040B		±10	±43	
		LM4040C			±25	±58	
		LM4040D			±50	±99	
I <sub>R_MIN</sub>	Minimum Operating Current				45	65	μΑ
$\Delta V_R / \Delta T$	Reverse Breakdown Voltage	I <sub>R</sub> = 10 mA			±30		ppm/°C
	Temperature Coefficient	I <sub>R</sub> = 1 mA	LM4040A, B, C		±20	±100	
			LM4040D		±20	±150	
		I <sub>R</sub> = 100 μA	-		±15		

 Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

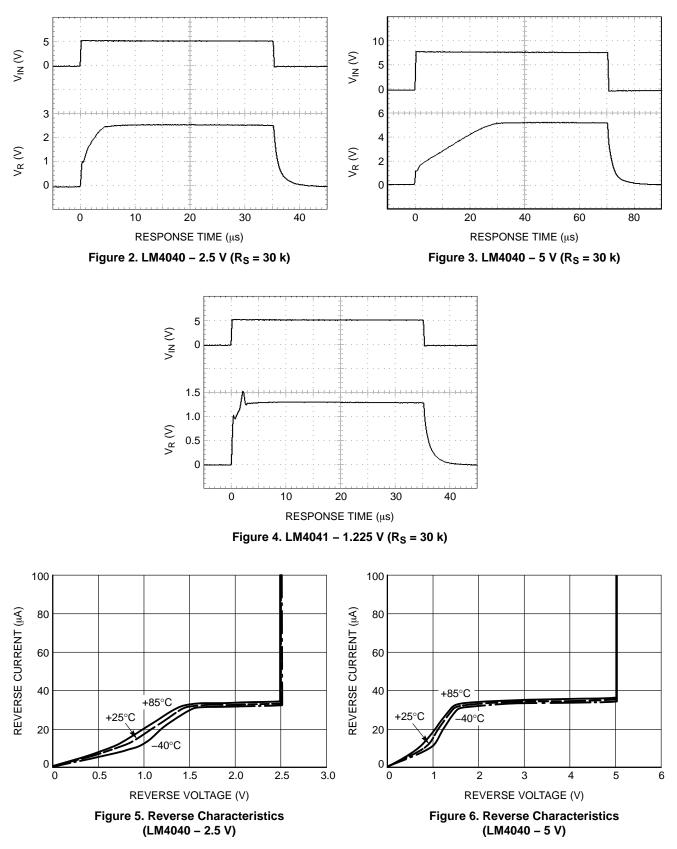
### Table 5. DC ELECTRICAL CHARACTERISTICS

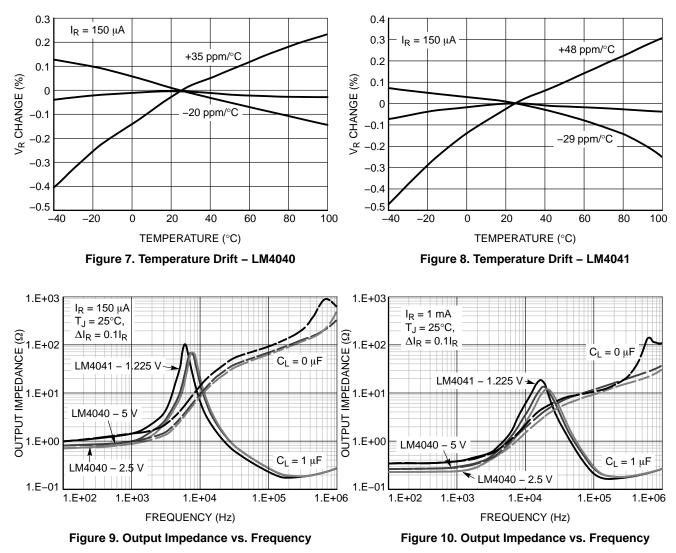
(I<sub>R</sub> = 100  $\mu$ A, T<sub>A</sub> = -40°C to +85°C, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

					Limits			
Symbol	Parameter	Test (	Conditions	Min	Тур	Max	Units	
5.000 V		-						
$\Delta V_R / \Delta I_R$	Reverse Breakdown Voltage	$I_{R_{MIN}} \leq I_{R} \leq$	LM4040A, B, C		0.5	1.4	mV	
	Change with Operating Current	Change with Operating Current 1 m	1 mA	LM4040D		05	1.8	
		1 mA ≤ I <sub>R</sub> ≤ 15 mA	LM4040A, B, C		3.5	12		
			LM4040D		3.5	15		
Z <sub>R</sub>	Reverse Dynamic Impedance	I <sub>R</sub> = 1 mA,	LM4040A, B		0.5	1.1	Ω	
		f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	LM4040C		0.5	1.1		
			LM4040D		0.5	1.5		
e <sub>N</sub>	Wideband Noise	I <sub>R</sub> = 100 μA, 10	Hz ≤ f ≤ 10 KHz		800		$\mu V_{RMS}$	
$\Delta V_{R}$	Reverse Breakdown Voltage Long Term Stability	T = 1000 h			120		ppm	
V <sub>HYST</sub>	Thermal Hysteresis (Note 2)	$\Delta T = -40^{\circ}C$ to	+125°C		0.08		%	

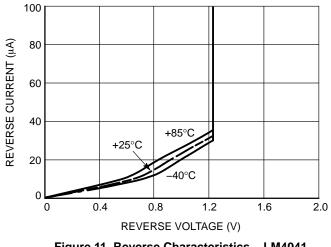
Guaranteed by design.
 Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.

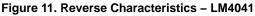
### **TYPICAL PERFORMANCE CHARACTERISTICS**





### **TYPICAL PERFORMANCE CHARACTERISTICS**





### **Device Description**

The LM404x shunt references use ON Semiconductor's floating gate (EEPROM) technology to produce a capacitor which stores an accurate and stable voltage that is used as the reference voltage for a control amplifier and shunt N–channel FET.

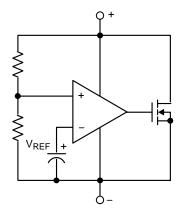


Figure 12. Functional Block Diagram

The device operates like a zener diode; maintaining a fixed voltage across its output terminals when biased with 60  $\mu$ A to 15 mA of reverse current. The LM404x will also act like a silicon diode when forward biased with currents up to 10 mA.

#### **Applications Information**

The LM404x's internal pass transistor maintains a constant output voltage by sinking the necessary amount of current across a source resistor. The source resistance (RS) is set by the load current range ( $I_{LOAD}$ ), supply voltage (VS) variations, LM404x's terminal voltage (VR), and desired quiescent current.

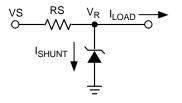


Figure 13. Typical Operating Circuit

To select a value of RS, set VS at its minimum value and  $I_{LOAD}$  at its maximum. Be sure to maintain a minimum operating current of 60  $\mu$ A through LM404x at all times, as LM404x uses this current to power its internal circuitry. The RS value should be large enough to keep  $I_{SHUNT}$  less than 15 mA for proper regulation when VS is maximum and  $I_{LOAD}$  is at a minimum. Therefore, the value of RS is bounded by the following equation:

$$\frac{\left(V_{S(min)} - V_{R}\right)}{\left(60 \ \mu A \ + \ I_{LOAD(max)}\right)} > RS$$

and

$$RS > \frac{\left(V_{S(max)} - V_{R}\right)}{\left(15 \text{ mA} + I_{LOAD(min)}\right)}$$

Choosing a larger resistance minimizes the power dissipated in the circuit by reducing the shunt current.

### **Output Capacitance**

The LM404x does not require an external capacitor for frequency stability and is stable for any output capacitance.

#### **Effect of Temperature**

LM404x has an output voltage temperature coefficient of typically  $\pm 15$  to  $\pm 30$  ppm/°C meaning the LM404x's output voltage will change by 50 – 100  $\mu$ V/°C for a 3.300 V regulator. The polarity of this temperature induced voltage shift can vary from device to device, some moving in the positive direction and others in the negative direction.

Part Number	Specific Device Marking	Voltage	Accuracy	Max Drift	Temperature Range	Package (Note 3)
LM4040BTB-250GT3		2.500 V	±0.2%	100 ppm/°C		SOT-23-3
LM4040BTB-300GT3	4	3.000 V	±0.2%	100 ppm/°C	−40°C to 85°C	
LM4040BTB-409GT3	4L	4.096 V	±0.2%	100 ppm/°C	-40°C 10 85°C	
LM4040BTB-500GT3		5.000 V	±0.2%	100 ppm/°C		
LM4041 <b>C</b> SD-122GT3	4M	1.225 V	±0.5%	100 ppm/°C	-40°C to 85°C	SC-70-5

#### **Table 6. ORDERING INFORMATION**

3. Tape & Reel, 3,000 Units / Reel

4. All packages are RoHS-compliant (Lead-free, Halogen-free).

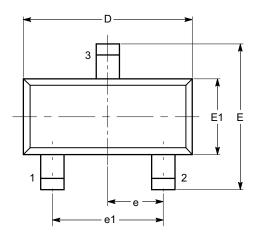
5. The standard lead finish is NiPdAu.

 For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

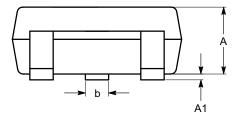
7. For detailed information and a breakdown of device nomenclature and numbering systems, please see the ON Semiconductor Device Nomenclature document, TND310/D, available at www.onsemi.com

### PACKAGE DIMENSIONS

SOT-23, 3 Lead CASE 527AG ISSUE O



TOP VIEW

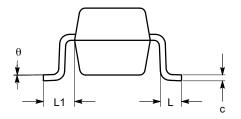


SIDE VIEW

#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
   (2) Complies with JEDEC TO-236.

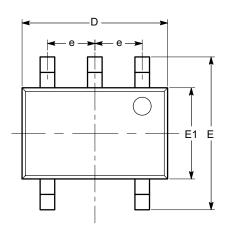
SYMBOL	MIN	NOM	МАХ			
А	0.89		1.12			
A1	0.013		0.10			
b	0.37		0.50			
с	0.085		0.18			
D	2.80		3.04			
E	2.10		2.64			
E1	1.20		1.40			
е	0.95 BSC					
e1	1.90 BSC					
L	0.40 REF					
L1	0.54 REF					
θ	0°		8°			



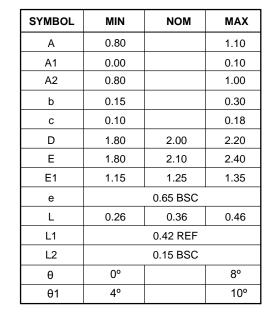
END VIEW

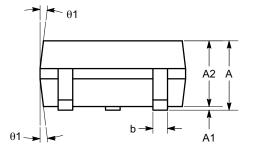
### PACKAGE DIMENSIONS

#### SC-88A (SC-70 5 Lead), 1.25x2 CASE 419AC ISSUE A









SIDE VIEW

#### Notes:

(1) All dimensions are in millimeters. Angles in degrees.

(2) Complies with JEDEC MO-203.

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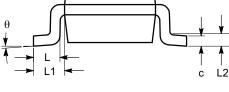
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END VIEW

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